



DONGGUAN NANJING ELECTRONICS LTD.,

PNP General Purpose Transistor

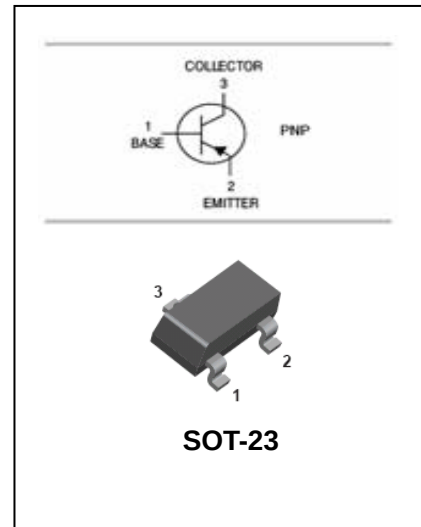
MMBT5401

FEATURES

- Epitaxial planar die construction.
- Complementary NPN type available (MMBT5551).
- Also available in lead free version.

APPLICATIONS

- Ideal for medium power amplification and switching



ORDERING INFORMATION

Type No.	Marking	Package Code
MMBT5401	2L	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT
V_{CBO}	collector-base voltage	-160	V
V_{CEO}	collector-emitter voltage	-150	V
V_{EBO}	emitter-base voltage	-5	V
I_C	collector current (DC)	-0.6	A
P_C	Collector dissipation	0.3	W
T_j, T_{stg}	junction and storage temperature	-55-150	°C

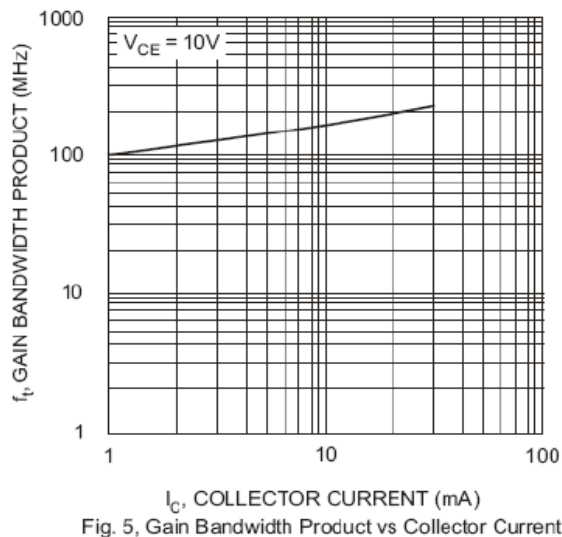
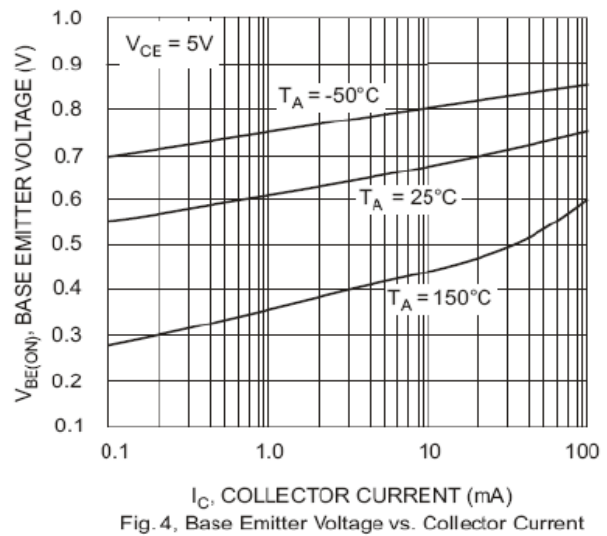
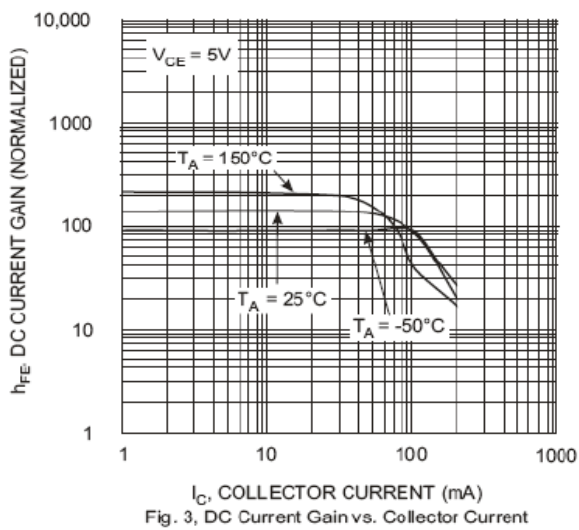
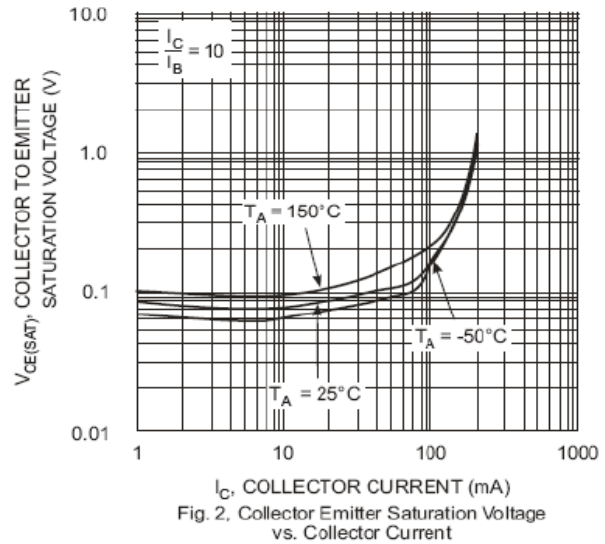
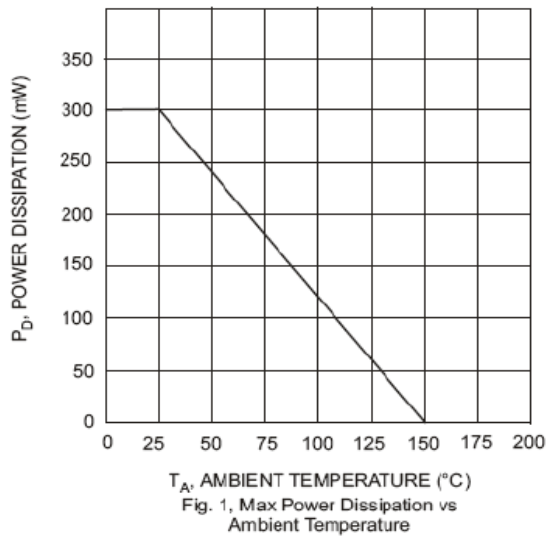
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu A, I_E = 0$	-160		
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -1mA, I_B = 0$	-150		
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -10\mu A, I_C = 0$	-5		
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -120V$	-	-0.1	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -4V$	-	-0.1	μA
h_{FE}	DC current gain	$V_{CE} = -5V; I_C = -1mA$ $V_{CE} = -5V; I_C = -10mA$ $V_{CE} = -5V; I_C = -50mA$	50 60 50	- 250 -	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = -50mA; I_B = -5mA$	-	-0.5	V
$V_{BE(sat)}$	base-emitter saturation voltage	$I_C = -50mA; I_B = -5mA$	-	-1	V
f_T	transition frequency	$I_C = -10mA; V_{CE} = -5V;$ $f = 30MHz$	100	-	MHz

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TYPICAL CHARACTERISTICS @ $T_A=25^\circ\text{C}$ unless otherwise specified



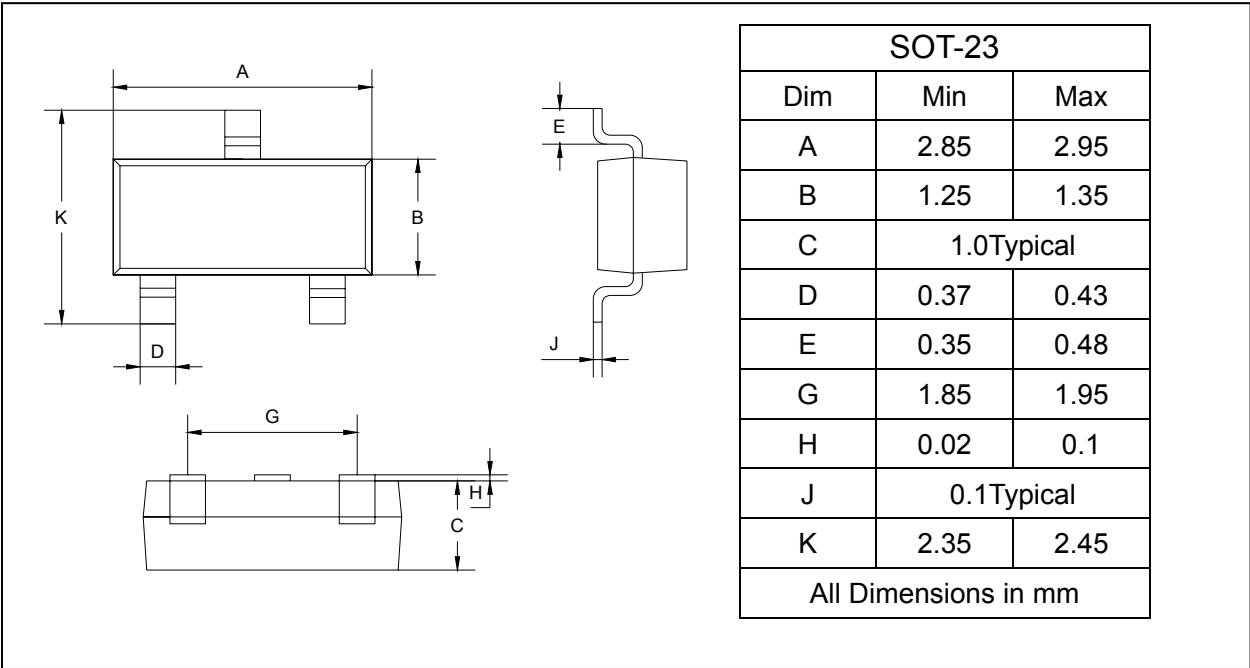
PNP General Purpose Transistor

MMBT5401

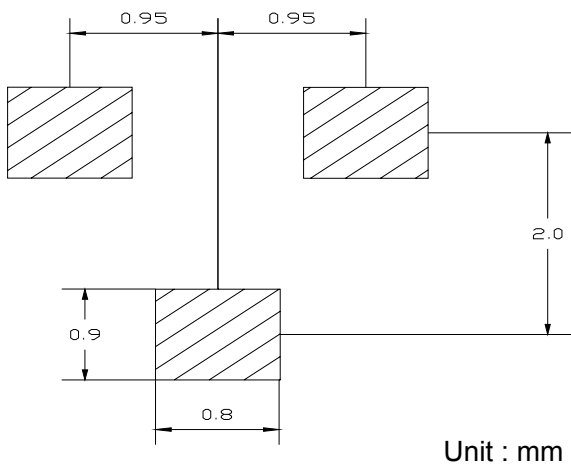
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
MMBT5401	SOT-23	3000/Tape&Reel